Abstracts

High saturation power 1.3-/spl mu/m MQW electroabsorption waveguide modulators on GaAs substrates

K.K. Loi, L. Shen, H.H. Wieder and W.S.C. Chang. "High saturation power 1.3-/spl mu/m MQW electroabsorption waveguide modulators on GaAs substrates." 1997 Microwave and Guided Wave Letters 7.10 (Oct. 1997 [MGWL]): 320-322.

An analog InGaAs-InAlAs multiple-quantum-well electroabsorption waveguide modulator operating at 1.32-/spl mu/m wavelength has been designed, fabricated, and characterized for the first time on a GaAs substrate. A typical 3-/spl mu/m-wide 115-/spl mu/m-long device exhibits a high optical saturation power in excess of 17 mW and a 3-dB electrical bandwidth of 20 GHz. An equivalent half-wave voltage V/sub /spl pi// of 2.8 V has also been achieved.

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